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(54) **MANUFACTURING METHOD OF DISPLAY
DEVICE AND DISPLAY DEVICE**

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(57) **ABSTRACT**

A manufacturing method of a display device includes forming a light emitting element layer on a substrate, co-depositing bismuth (Bi) and ytterbium (Yb) on the light emitting element layer to form a first inorganic absorbing layer, and forming a reflection control layer on the first inorganic absorbing layer. In the co-depositing, a deposition temperature of bismuth (Bi) is in a range of about 500° C. to about 850° C., a deposition temperature of ytterbium (Yb) is in a range of about 300° C. to about 550° C., and an extinction coefficient of the first inorganic absorbing layer is less than or equal to about 3.

